

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)  
(Use several sheets if necessary)ATTY DOCKET NO.  
35.C10530C/D2APPLICATION NO.  
Div. of 08/863,717APPLICANT  
KIYOFUMI SAKAGUCHI, ET AL.FILING DATE  
September 29, 1998GROUP  
NYA

8823

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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G	5453394	9/95	Yonehara, et al.	—	—	
G	5277748	1/94	Sakaguchi, et al.	—	—	
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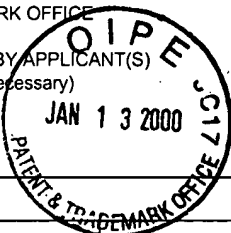
EXAMINER

FOURSON

DATE CONSIDERED

4/30/01

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ATTY DOCKET NO. 35.C10530C/D2

APPLICATION NO.  
09/161,774

APPLICANT...KIYOFUMI SAKAGUCHI ET AL.

FILING DATE September 29, 1998

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G	5,248,621	09/28/93	Sano	437	3	
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G		Extended Abstracts (the 57 <sup>th</sup> Autumn Meeting, 1996); The Japan Society of Applied Physics (Abstr. 8a-V-8) (with translation)
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G		T. Ito et al. "Porous Silicon Crystal Prepared by Anodization", <u>Applied Physics</u> (Japanese) vol. 57 no. 11 (1988) (no translation)
EXAMINER		DATE CONSIDERED
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